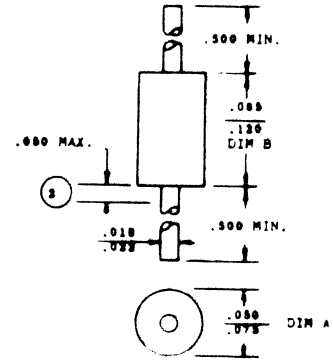


Absolute Maximum Ratings	
5082-2800 Series	
P _A Power Dissipation at T _A = 25°C	250 mW (Note 1)
Derate 1.43 mW/°C for T _A = 25°C to 200°C	
T _A Operating Temp. Range	-65 to +200°C
T _{STG} Storage Temp. Range	-65 to +200°C
Note 1. As measured using an infinite heat sink.	

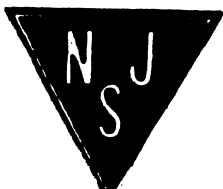
Mechanical Specifications

HERMETIC GLASS DO-35 PACKAGE



Electrical Specifications at T_A = 25°C

Diode Type	Specification	Symbol	Min	Max	Units	Test Conditions
5082-2800 2810 2811	Breakdown Voltage	V _{BR}	70 20 15		Volts	I _B = 10 μA
5082-2800 2810 2811	Forward Voltage	V _F		410 410 410	mV	I _F = 1 mA
5082-2800 2810 2811	Forward Current	I _F	15 35 20		mA	V _F = 1 volt (note 1)
5082-2800 2810 2811	Reverse Leakage Current	I _S		200 100 100	nA	V _R = 50 V V _R = 15 V V _R = 8 V
5082-2800 2810 2811	Capacitance	C _{T(F)}		2.0 1.2 1.2	pF	V _R = 0 V and f = 1 MHz
5082-2800 2810 2811	Effective Minority Carrier Lifetime	τ		100 100 100	psec	I _F = 5 mA Krakauer Method



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